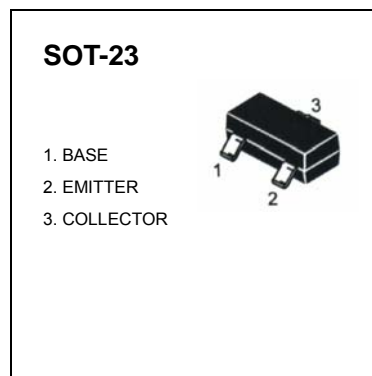


## TRANSISTOR (PNP)

### FEATURES

- Low frequency power amplifier application
- Power switching application



### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-35	V
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current –Continuous	-0.8	A
$P_{C^*}$	Collector Dissipation	200	mW
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	100		320	
	$h_{FE(2)}$	$V_{CE}=-1\text{V}, I_C=-800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-20\text{mA}$			-0.4	V
Base- emitter voltage	$V_{BE}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	-0.5		-0.8	V
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$ ,		120		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

### CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320
MARKING	IO	IY

# Typical Characteristics

